# 2N6284 (NPN); 2N6286, 2N6287 (PNP)

Preferred Device

# **Darlington Complementary Silicon Power Transistors**

These packages are designed for general-purpose amplifier and low-frequency switching applications.

#### Features

- High DC Current Gain @  $I_C = 10 \text{ Adc} h_{FE} = 2400 \text{ (Typ)} 2N6284$ = 4000 (Typ) - 2N6287
- Collector–Emitter Sustaining Voltage V<sub>CEO(sus)</sub> = 100 Vdc (Min)
- Monolithic Construction with Built-In Base-Emitter Shunt Resistors
- Pb-Free Packages are Available\*

### MAXIMUM RATINGS (Note 1)

Rating		Symbol	Value	Unit
Collector-Emitter Voltage	2N6286 2N6284/87	V <sub>CEO</sub>	80 100	Vdc
Collector-Base Voltage	2N6286 2N6284/87	V <sub>CB</sub>	80 100	Vdc
Emitter-Base Voltage		$V_{EB}$	5.0	Vdc
Collector Current – Contin Peak	Ι <sub>C</sub>	20 40	Adc	
Base Current		Ι <sub>Β</sub>	0.5	Adc
Total Power Dissipation @ Derate above 25°C	PD	160 0.915	W W/°C	
Operating and Storage Ten Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +200	°C	

#### THERMAL CHARACTERISTICS (Note 1)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.09	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

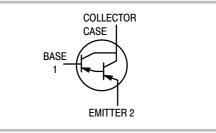
1. Indicates JEDEC Registered Data.

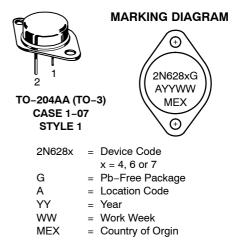


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## 20 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 100 VOLTS, 160 WATTS



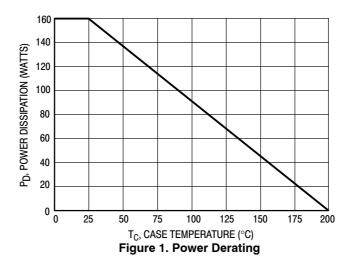


#### ORDERING INFORMATION

Device	Package	Shipping
2N6284	TO-3	100 Units/Tray
2N6284G	TO-3 (Pb-Free)	100 Units/Tray
2N6286	TO-3	100 Units/Tray
2N6286G	TO–3 (Pb–Free)	100 Units/Tray
2N6287	TO-3	100 Units/Tray
2N6287G	TO-3 (Pb-Free)	100 Units/Tray

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## 2N6284 (NPN); 2N6286, 2N6287 (PNP)



#### **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted) (Note 2)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage $(I_C = 0.1 \text{ Adc}, I_B = 0)$	2N6286 2N6284, 2N6287	V <sub>CEO(sus)</sub>	80 100		Vdc
Collector Cutoff Current $(V_{CE} = 40 \text{ Vdc}, I_B = 0)$ $(V_{CE} = 50 \text{ Vdc}, I_B = 0)$		I <sub>CEO</sub>		1.0 1.0	mAdc
$      Collector Cutoff Current \\ (V_{CE} = Rated V_{CB}, V_{BE(off)} = 1.5 \text{ Vdc}) \\ (V_{CE} = Rated V_{CB}, V_{BE(off)} = 1.5 \text{ Vdc}, T_C = 150^{\circ}\text{C}) $		I <sub>CEX</sub>		0.5 5.0	mAdc
Emitter Cutoff Current (V <sub>BE</sub> = 5.0 Vdc, I <sub>C</sub> = 0)		I <sub>EBO</sub>	-	2.0	mAdc
ON CHARACTERISTICS (Note 3)					
DC Current Gain (I <sub>C</sub> = 10 Adc, V <sub>CE</sub> = 3.0 Vdc) (I <sub>C</sub> = 20 Adc, V <sub>CE</sub> = 3.0 Vdc)		h <sub>FE</sub>	750 100	18,000 -	-
Collector-Emitter Saturation Voltage $(I_C = 10 \text{ Adc}, I_B = 40 \text{ mAdc})$ $(I_C = 20 \text{ Adc}, I_B = 200 \text{ mAdc})$		V <sub>CE(sat)</sub>		2.0 3.0	Vdc
Base–Emitter On Voltage $(I_C = 10 \text{ Adc}, V_{CE} = 3.0 \text{ Vdc})$		V <sub>BE(on)</sub>	_	2.8	Vdc
Base-Emitter Saturation Voltage $(I_C = 20 \text{ Adc}, I_B = 200 \text{ mAdc})$		V <sub>BE(sat)</sub>	-	4.0	Vdc
DYNAMIC CHARACTERISTICS					•
Magnitude of Common Emitter Small–Signal Short–Circuit Forward Current Transfer Ratio (I <sub>C</sub> = 10 Adc, V <sub>CE</sub> = 3.0 Vdc, f = 1.0 MHz)		h <sub>fe</sub>	4.0	-	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 0.1 MHz)	2N6284 2N6286, 2N6287	C <sub>ob</sub>		400 600	pF
Small–Signal Current Gain ( $I_C = 10 \text{ Adc}, V_{CE} = 3.0 \text{ Vdc}, f = 1.0 \text{ kHz}$ )		h <sub>fe</sub>	300	-	-

2. Indicates JEDEC Registered Data.

3. Pulse test: Pulse Width = 300  $\mu$ s, Duty Cycle = 2%

### 2N6284 (NPN); 2N6286, 2N6287 (PNP)

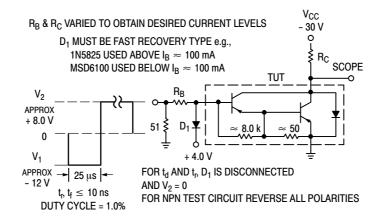
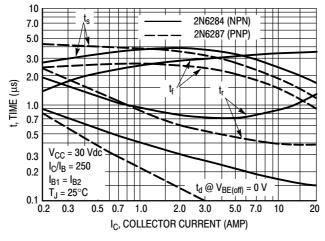


Figure 2. Switching Times Test Circuit





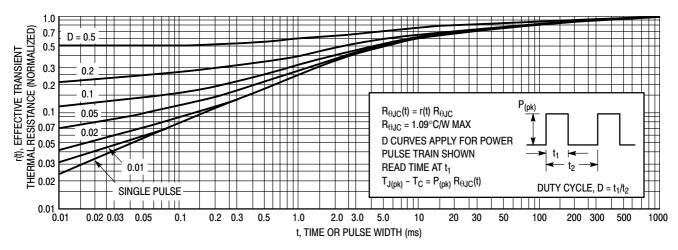


Figure 4. Thermal Response

#### **ACTIVE-REGION SAFE OPERATING AREA**

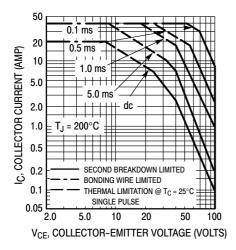
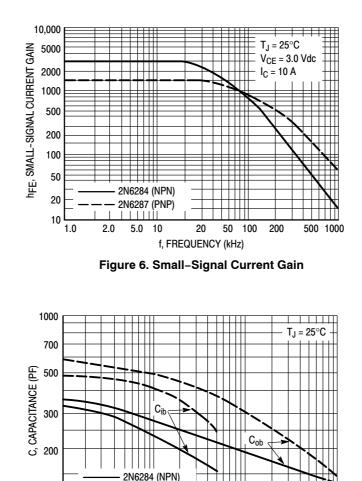


Figure 5. 2N6284, 2N6287

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C$  –  $V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e. the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on  $T_{J(pk)} = 200^{\circ}$ C;  $T_{C}$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} < 200^{\circ}$ C.  $T_{J(pk)}$  may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.



V<sub>R</sub>, REVERSE VOLTAGE (VOLTS) Figure 7. Capacitance

5.0

20

50 100

10

2.0

2N6287 (PNP)

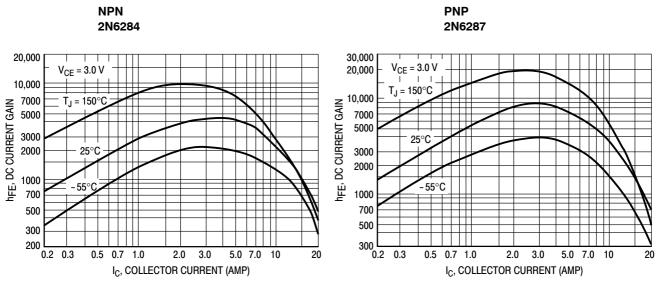
1.0

0.5

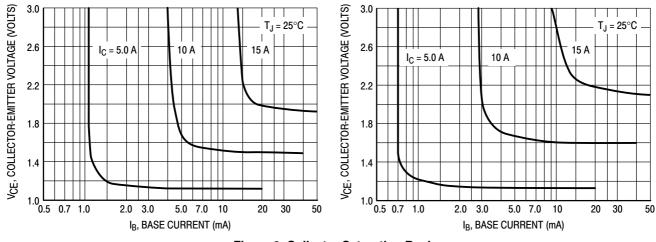
100

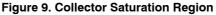
0.1

0.2









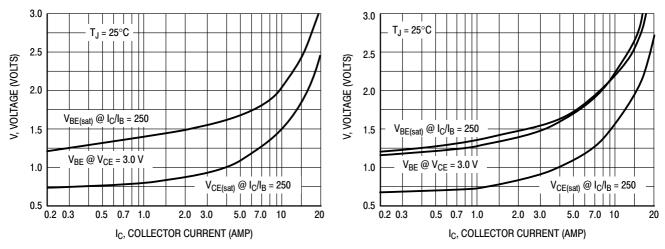


Figure 10. "On" Voltages

### 2N6284 (NPN); 2N6286, 2N6287 (PNP)

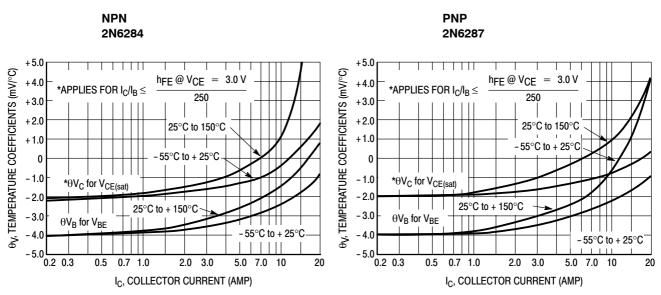
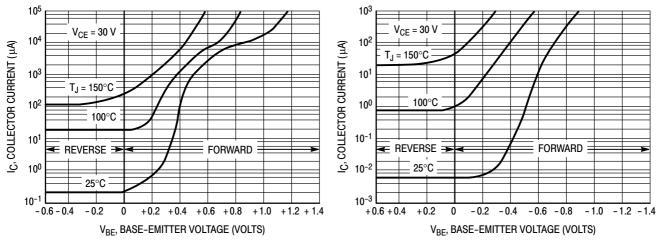
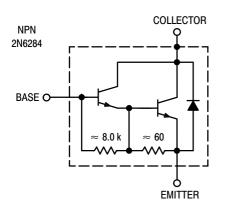


Figure 11. Temperature Coefficients







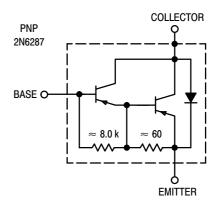


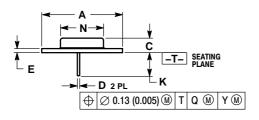
Figure 13. Darlington Schematic

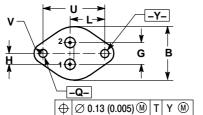




DATE 05/18/1988

SCALE 1:1





#### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

2. CONTROLLING DIMENSION: INCH.

 ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

	INCHES		ES MILLIMETER	
DIM	MIN	MAX	MIN	MAX
Α	1.550 REF		39.37 REF	
В		1.050		26.67
С	0.250	0.335	6.35	8.51
D	0.038	0.043	0.97	1.09
Е	0.055	0.070	1.40	1.77
G	0.430 BSC		10.92 BSC	
Η	0.215 BSC		5.46	BSC
Κ	0.440	0.480	11.18	12.19
L	0.665	0.665 BSC		BSC
Ν		0.830		21.08
Q	0.151	0.165	3.84	4.19
U	1.187 BSC		30.15	BSC
V	0.131	0.188	3.33	4.77

STYLE 1:	STYLE 2:	STYLE 3:	Style 4:	STYLE 5:
PIN 1. BASE	PIN 1. BASE	PIN 1. GATE	Pin 1. ground	PIN 1. CATHODE
2. EMITTER	2. COLLECTOR	2. SOURCE	2. input	2. EXTERNAL TRIP/DELAY
CASE: COLLECTOR	CASE: EMITTER	CASE: DRAIN	Case: output	CASE: ANODE
STYLE 6:	Style 7:	STYLE 8:	STYLE 9:	
PIN 1. GATE	Pin 1. Anode	PIN 1. CATHODE #1	PIN 1. ANODE #1	
2. EMITTER	2. Open	2. CATHODE #2	2. ANODE #2	
CASE: COLLECTOR	Case: Cathode	CASE: ANODE	CASE: CATHODE	

TO-204 (TO-3) CASE 1-07 ISSUE Z

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 2N6051
 MJ2501
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